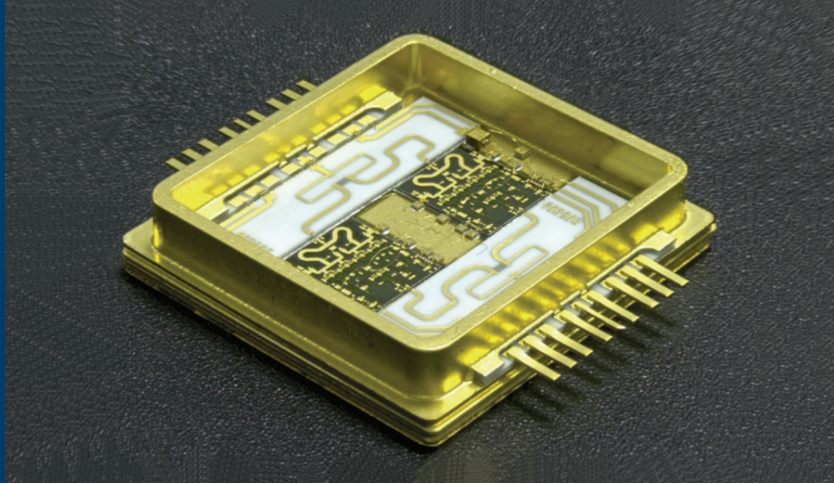


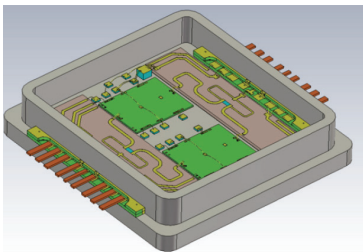
GaN High Power Amplifiers up to 50W in hermetic package



Innovative product solutions

Design Know How

- Control interfaces for HPA fast switching times (<10ns)
- 3D simulation for optimum integration
- RF transitions optimized up to 18GHz
- Thermally optimized

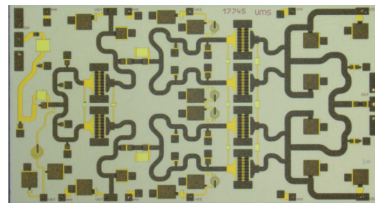


Performance

High level of performance in short pulsed mode:

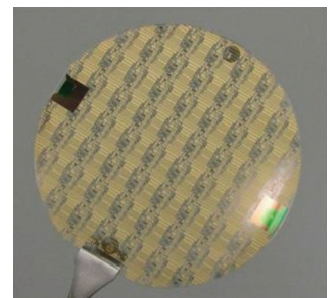
- 50W in X-Band / 35% PAE
- 30W in Ku Band / 25% PAE

RF ports matched to 50 ohms



Technology

- 0.25µm GaN on SiC
- Proprietary technology
- European source
- Hermetic package
- Internal assembly line:
 - Eutectic die attach
 - Micro-wire bondings
 - Package sealing and leak testing



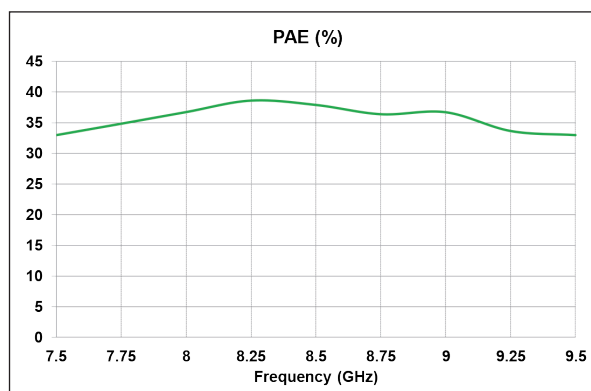
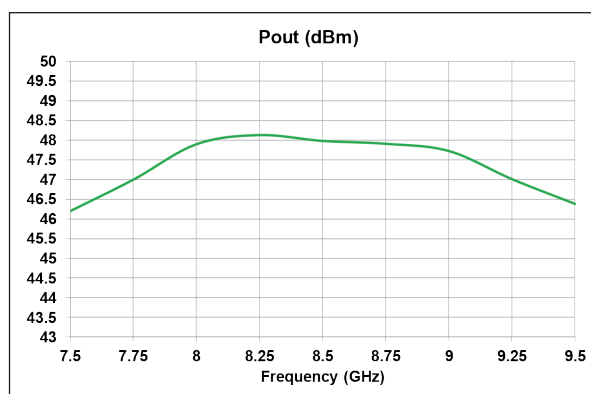
Parts description

Package thermal management performed on Cu-Mo-Cu base.

Ceramic-metal Flangeless package dimensions: 17.4 x 17.9 x 4.5 mm.

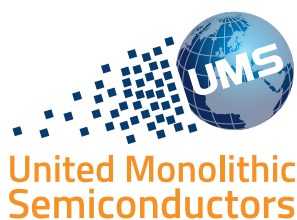
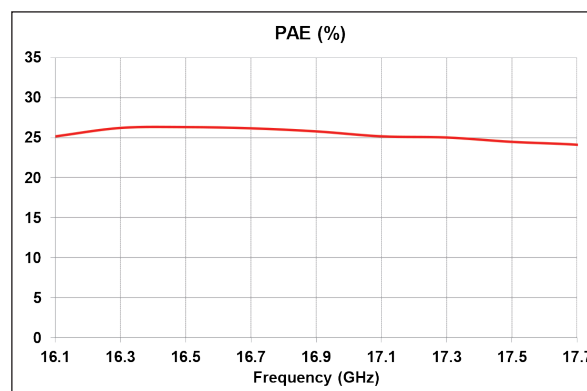
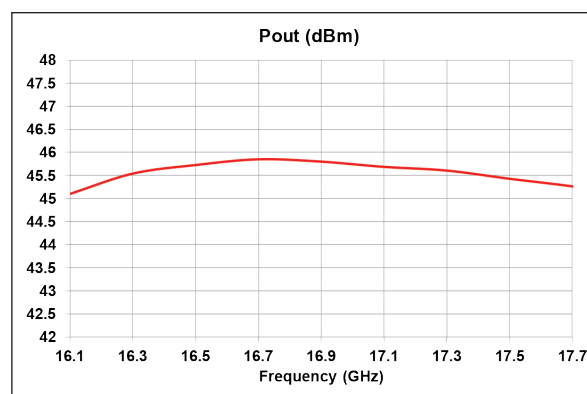
Main Features for X Band HPA

- Psat: 47.5dBm @Pin=28dBm
- PAE: 35% @Pin=28dBm
- Power Gain: 19dB
- Small Signal Gain: 27dB
- Bias: Vd=30V, Idq=2.2A, Idsat=5A, Vg#-3.2V
- Short Vg pulses thru control interfaces



Main Features for Ku Band HPA

- Psat: 45dBm @Pin=33dBm
- PAE: 25% @Pin=33dBm
- Power Gain: 12dB
- Small Signal Gain: 20dB
- Bias: Vd=30V, Idq=2.2A, Idsat=4.5A, Vg#-3.2V
- Short Vg pulses thru control interfaces



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